What is claimed is:

1. A liquid crystal display device, comprising:

an upper substrate including:

a) a switching element on the upper substrate

b) a passivation film formed over the whole surface of the upper substrate while covering the switching element;

c) a pixel electrode on the passivation film;

d) a black matrix formed over the switching element;

e) a color filter formed over the pixel electrode; and

f) a first orientation film formed on the black matrix and the pixel electrode;

a lower substrate having a common electrode and a second orientation film, the orientation film formed on the common electrode; and

a liquid crystal layer interposed between the upper and lower substrates.

2. The liquid crystal display device of claim 1, wherein the switching element is a thin film transistor, the thin film transistor having a gate electrode formed on the upper substrate, a gate insulating layer formed on the exposed surface of the upper substrate while covering the gate electrode, a semiconductor layer formed over the gate electrode, a source electrode overlapping one end portion of the semiconductor layer, and a drain electrode overlapping the other end portion of the semiconductor layer.

3. The liquid crystal display device of claim 2, further comprising a first light absorbing film formed under the gate electrode, a second light absorbing film formed

under the source electrode, and a third light absorbing film formed under the drain electrode.

4. The liquid crystal display device of claim 2, further comprising, a first light absorbing film formed under the gate electrode and a second light absorbing film formed under the semiconductor layer.

5. The liquid crystal display device of claim 3, further comprising, a gate line connected with the gate electrode and a data line connected with the source electrode, the first light absorbing film formed under the gate line, the second light absorbing film formed under data line.

6. The liquid crystal display device of claim 4, further comprising, a gate line connected with the gate electrode and a data line connected with the source electrode, the first light absorbing film formed under the gate line, the second light absorbing film formed under data line.

7. The liquid crystal display device of claim 5, further comprising, a back light device for supplying light to the liquid crystal layer.

8. The liquid crystal display device of claim 7, wherein the common electrode and the pixel electrode are made of indium tin oxide (ITO).

9. The liquid crystal display device of claim 1, wherein the common electrode

is made of an opaque conductive material.

10. The liquid crystal display device of claim 3, wherein the common electrode is made of an opaque conductive material.

11. The liquid crystal display device of claim 4, wherein the common electrode is made of an opaque conductive material.

12. A method of manufacturing a liquid crystal display device which comprises an array of thin film transistors and an array of pixel electrodes including:

forming a gate line and a gate electrode on an upper substrate, the gate electrode extending from the gate electrode;

forming a gate insulating layer on the exposed surface of the upper substrate while covering the gate line and the gate electrode;

forming a semiconductor layer over the gate electrode;

forming a data line and source and drain electrodes, the source electrode overlapping one end portion of the semiconductor layer, the drain electrode overlapping the other end portion of the semiconductor layer, the source and drain electrodes spaced apart from each other, the source electrode extending from the data line;

forming a passivation film over the whole surface of the upper substrate while covering the source and drain electrodes, the passivation film having a contact hole on the drain electrode;

forming a pixel electrode on the passivation film, the pixel electrode electrically connected with the drain electrode through the contact hole;

forming a color filter on the pixel electrode;

forming a black matrix over the thin film transistor;

forming a first orientation film on the color filters and the black matrices;

forming a common electrode on a lower substrate;

forming a second orientation film on the common electrode;

aligning the upper substrate turned upside down with the lower substrate so that the first orientation film of the first substrate is opposite to the second orientation film of the second substrate with a gap there between; and

injecting a liquid crystal between the upper substrate and the lower substrate.

13. The method of claim 12, further comprising:

forming a first light absorbing film between the upper substrate and the gate electrode; and

forming a second light absorbing film between the semiconductor layer and the source and drain electrodes.

14. The method of claim 12, further comprising:

forming a first light absorbing film between the upper substrate and the gate electrode; and

forming a second light absorbing film between the semiconductor layer and the gate insulating layer.

15. The method of claim 13, wherein the common electrode and the pixel electrode are made of indium tin oxide.

16. The method of claim 14, wherein the common electrode and the pixel electrode are made of indium tin oxide.

17. The method of claim 13, wherein the common electrode is made of an opaque conductive material.

18. The method of claim 14, wherein the common electrode is made of an opaque conductive material.